SEE FLUX AND SPECTRAL HARDNESS CALIBRATION OF NEUTRON SPALLATION AND MIXED FIELD FACILITIES

Matteo Cecchetto

R. García Alía, P. Fernández-Martínez, R. Ferraro, S. Danzeca



Indico link: https://indico.cern.ch/event/760345/



Introduction

- Single Event Effect (SEE) failure rate for electronic components to be used in mixed field environments (accelerator) has to be quantified by reproducing the spectrum condition in dedicated test facilities.
- The availability of a method to compare different radiation environments is essential, because differences in neutron and High Energy Hadrons (HEH>20 MeV) spectra can play an important role.
- The approach applied for the characterization of both spallation (ChipIR) and mixed filed (CHARM) facilities relies in **employing SEU and SEL based detectors**:

SEU: The memory is assumed to be equally sensitive to HEH above 20 MeV and a weighting function has to be accounted for the intermediate energy neutrons, considered from 0.2 MeV to 20 MeV, where the cross section is strongly energy dependent.

$$\varphi_{HEHeq} = \int_{0.2MeV}^{20MeV} w(E) \frac{d\varphi_n(E)}{dE} dE + \int_{20MeV}^{+\infty} \frac{d\varphi_{HEH}(E)}{dE} dE$$

Intermediate energy neutrons start to be a major concern with scaling of technology.

SEL: COTS memories with a strong energy dependence on the SEL cross section are employed to correlate the spectral hardness of the facilities, supported by a FLUKA model.



ChipIr facility

- The ChipIr (Chip Irradiation) facility (UK), provides a broad neutron atmospheric like spectrum.
 - Energies from the thermal neutrons up to 800 MeV
 - Neutrons produced by colliding protons against a tungsten target.
 - The flux was measured using multi-foils activation.
- It was investigated in order to verify its capability of reproducing the SEU and SEL cross sections typically observed in mixed field environments, such as CHARM.



Figure 1: ChipIr spectrum



CHARM facility

- CHARM generates a **mixed-field** mainly composed by **neutrons, protons** and **pions** from the interaction of 24 GeV proton beam with a copper target.
- R10 (hard spectrum) and G0 (soft spectrum) were employed.









ChipIR flux cross-calibration

- The flux calibration was carried out with:
 - 1) **ESA SEU Monitor** (0.25 µm SRAM memory)
 - 2) RadMon system (Toshiba 400 nm, Cypress 90 nm).
 - Excellent HEHeq agreement within 1% was obtained with the RadMon;
 - **Thermal neutron flux within the uncertainty** (quite high due to the very low ThN flux compared to the HEH one).
- the intermediate energy neutron response (i.e. PTB at 5, 8 and 14 MeV) is essential to derive the flux from the ESA Monitor and Cypress memories.

	HEHeq [ThN [cm ⁻² /s]			
ESA M.	Spectrum	RadMon	Spectrum	RadMon	Spectrum
2.97×10 ⁶ ±20%	3.44×10 ⁶	3.09×10 ⁶ ±21%	3.07×10 ⁶	3.49×10 ⁴ +2.8×10 ⁵	1.60×10 ⁵



SPECTRAL HARDNESS ASSESSMENT – SEL measurements

- Samsung (180 nm) and Alliance (200 nm) are SRAM memories with a strong SEL cross section energy dependence due to the presence of tungsten, deployed as detectors.
- Assessment in:
 - <u>operational environments</u>: JEDEC, accelerator (UJ, RR alcoves)
 - <u>test facilities</u>: ChipIR, CHARM (G0, R10 positions).

UJ, RR, R10 and G0 are composed by neutrons, protons, pions.

The spectral hardness is quantified through the H_{10%} factor, representative of the energy above which 10% of the total HEH flux is still present in the spectrum, (visible in the reverse integral).

MeV	UJ	G0	ChipIr	JEDEC	RR	R10	Tunnel
H _{10%}	183	194	354	525	690	790	1800





SPECTRAL HARDNESS ASSESSMENT – SEL FLUKA simulations

- The FLUKA model retrieves the SEL XS up to several GeV, given the spectrum, Sensitive Volume (SV) thickness and geometrical parameters of the memories.
- The SV surface is 4x20 μm² and 0.48 μm³/cell of tungsten are considered.
 - **Measurements and simulations are in agreement** within 60% over a very broad energy and cross section range. Considering the experimental uncertainties of about 30%, the agreement is satisfactory.



Strong risk of qualifying components for SEEs in environments with a lower spectral hardness than the operational one.





SER induced by intermediate energy neutrons (1)

- SER on ESA Monitor, Toshiba, Cypress and a 65 nm FPGA* is evaluated in the 1-3 MeV, 1-10 MeV, 1-20 MeV energy intervals.
- 65nm FPGA with a G0-like spectrum

more than 50% of the SEUs are induced by neutrons below 20 MeV.





*D. Lambert et al., "Single Event Upsets Induced by a few MeV Neutrons in SRAMs and FPGAs," in 2017 IEEE Radiation Effects Data Workshop (REDW)

SER induced by intermediate energy neutrons (2)

- 1-3 MeV
- negligible impact.

• 1-10 MeV

- up to **12%** of SER for JEDEC, ChipIR, UJ.
- up to **36%** for CHARM G0 position.
- 1-20 MeV
- up to 21% of SER for ground level, 26% in accelerator applications and up to 54% for G0.

1-20 MeV	Spect %	ESA M.	Toshiba	Cypress	FPGA
UJ	39.4	9.6	12.3	7.1	18.4
G0	84.1	39.2	31	24.1	54.4
ChipIr	15.3	6.7	8.2	5	10.6
JEDEC	43.4	11.4	14.5	8.5	21.1
RR	56	17.8	13.5	9.9	26.5
R10	60.5	19.2	15.1	11.7	28.5

SER (%) impact of different spectra



Complementary work/Outlook

- The use of the Am-Be neutron source at CERN for SEU/SEE setup validation and evaluation of sensitivity to intermediate energy neutrons.
- The impact of thermal neutrons, for which an important sensitivity has been measured for highly integrated technologies.



Conclusions

- The procedure of cross-calibrating spallation and mixed-field facility through SEU detectors have been shown to be valid, with an excellent agreement on the HEH flux.
- The approach of determining the spectrum hardness through SEL measurements have been applied to ChipIr and CHARM. Compatible cross sections have been extracted through a FLUKA model, which therefore enables the calculations for environments in which measurements are not directly feasible, as for atmospheric and LCH areas.
- The spectral hardness of ChipIr enables for tests dedicated to some accelerator applications as shielded areas. However, tunnel and more energetic alcoves exhibit harder spectra, reproducible in CHARM.
- Considering the SEU rate of memories down to 65 nm, 1-10 MeV and 1-20 MeV ranges induce respectively up to 12% and 21% of the total SER in ground level applications, reaching up to 36% and 54% in accelerator environments.
- Intermediate energy neutrons (1-20 MeV) yield a larger SER contribution in accelerator rather than atmospheric applications.

